

TENTATIVE

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

1,048,576-WORD × 16-BIT EDO (HYPER PAGE) DYNAMIC RAM

DESCRIPTION

The TC51V18165CJ/CFT is an EDO (hyper page) dynamic RAM organized as 1,048,576 words by 16 bits. The TC51V18165CJ/CFT utilizes TOSHIBA's CMOS silicon gate process technology as well as advanced circuit techniques to provide wide operating margins, both internally and to the system user.

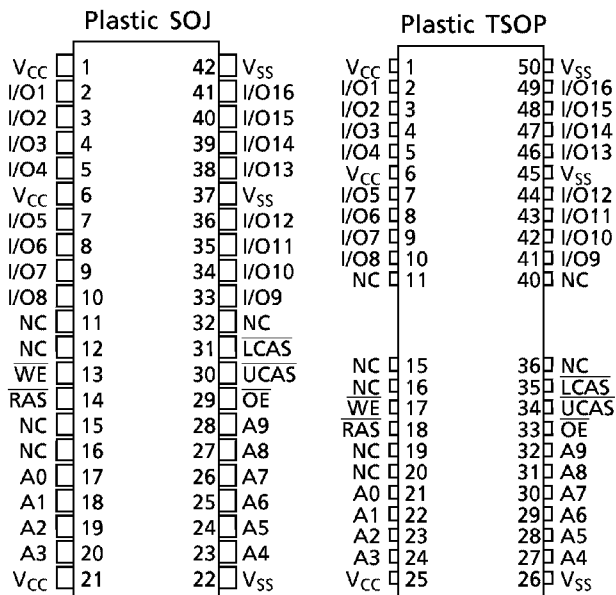
Multiplexed address inputs permit the TC51V18165CJ/CFT to be packaged in a 42-pin plastic SOJ or a 50-pin plastic TSOP. The package size provides high system bit densities and is compatible with widely available automated testing and insertion equipment. Other features include a single power supply of 3.3 V ± 0.3 V tolerance and direct interfacing with high performance logic families such as LVTTTL.

FEATURES

- 1,048,576 word by 16 bit organization
- Fast access time and cycle time
- Single power supply of 3.3 V ± 0.3 V with a built-in V_{BB} generator
- Low-power dissipation (max)
 - Operating: 810 mW (50 ns type)
 - : 666 mW (60 ns type)
 - Stand by : 1.8 mW (both devices)
- Unlatched outputs at cycle end allows two-dimensional chip selection
- Read-Modify-Write, CAS-before-RAS refresh, RAS-Only refresh, Hidden refresh and EDO(Hyper Page mode) capability
- All inputs and outputs TTL-compatible
- 1024 refresh cycles per 16 ms
- Package
 - CJ : SOJ42-P-400-1.27, 1.66 grams
 - CFT: TSOP II 50/44-P-400-0.80, 0.53 grams

		TC51V18165CJ/CFT	
		-50	-60
t _{RAC}	RAS Access Time	50 ns	60 ns
t _{AA}	Column Address Access Time	25 ns	30 ns
t _{CAC}	CAS Access Time	14 ns	17 ns
t _{RC}	Cycle Time	84 ns	104 ns
t _{HPC}	Hyper Page Mode Cycle Time	20 ns	25 ns

PIN ASSIGNMENT (TOP VIEW)



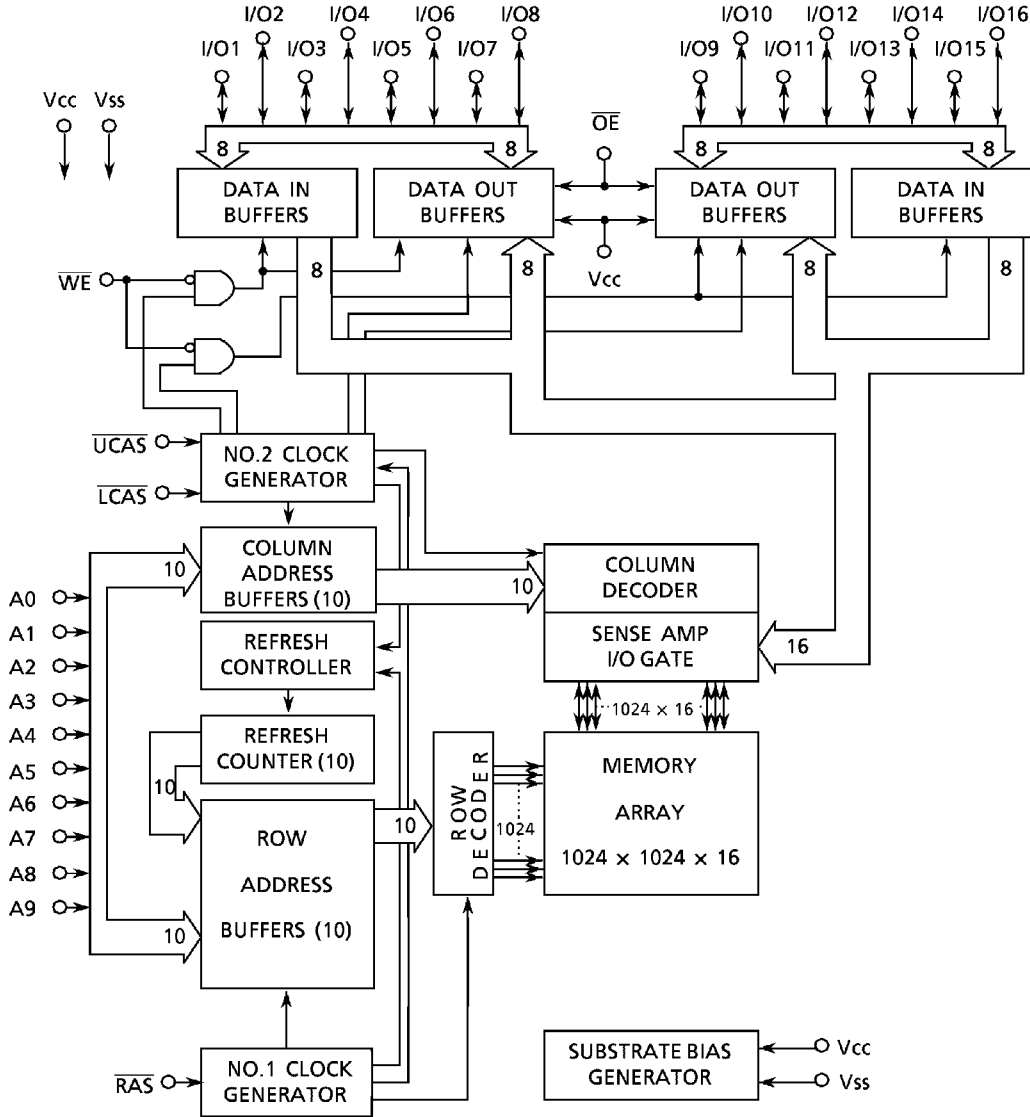
PIN NAMES

A0 to A9	Address Inputs
RAS	Row Address Strobe
UCAS	Column Address Strobe /Upper Byte Control
LCAS	Column Address Strobe /Lower Byte Control
WE	Write Enable
OE	Output Enable
I/O1 to I/O16	Data I/O
V _{CC}	Power (+ 3.3 V)
V _{SS}	Ground
N.C.	No Connection

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BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

ITEM	SYMBOL	RATING	UNIT	NOTES
Input Voltage	V_{IN}	-0.3 to $V_{CC} + 0.3$	V	1
Output Voltage	V_{OUT}	-0.3 to $V_{CC} + 0.3$	V	1
Power Supply Voltage	V_{CC}	-0.3 to 4.6	V	1
Operating Temperature	T_{OPR}	0 to 70	°C	1
Storage Temperature	T_{STG}	-55 to 150	°C	1
Soldering Temperature (10 s)	T_{SOLDER}	260	°C	1
Power Dissipation	P_D	1.0	W	1
Short Circuit Output Current	I_{OUT}	50	mA	1

DC RECOMMENDED OPERATING CONDITIONS ($T_a = 0^\circ$ to 70°C)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT	NOTES
V_{CC}	Supply Voltage	3.0	3.3	3.6	V	2
V_{IH}	Input High Voltage	2.2	-	$V_{CC} + 0.3^*$	V	2
V_{IL}	Input Low Voltage	-0.3**	-	0.8	V	2

* $V_{CC} + 1.2\text{ V}$ at pulse width $\leq 20\text{ ns}$ (pulse width is measured at V_{CC})

** -1.2 V at pulse width $\leq 20\text{ ns}$ (pulse width is measured at V_{SS})

DC CHARACTERISTICS ($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ$ to 70°C)

SYMBOL	PARAMETER		MIN	MAX	UNIT	NOTES
I _{CC1}	OPERATING CURRENT Average Power Supply Operating Current ($\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$, Address Cycling: $t_{RC} = t_{RC\text{ min}}$)	TC51V18165CJ/CFT-50	-	225	mA	3, 4, 5
		TC51V18165CJ/CFT-60	-	185		
I _{CC2}	STANDBY CURRENT Power Supply Standby Current ($\overline{\text{RAS}} = \overline{\text{UCAS}} = \overline{\text{LCAS}} = V_{IH}$)		-	1	mA	
I _{CC3}	$\overline{\text{RAS}}$ -ONLY REFRESH CURRENT Average Power Supply Current, $\overline{\text{RAS}}$ -Only Mode ($\overline{\text{RAS}}$ Cycling, $\overline{\text{UCAS}} = \overline{\text{LCAS}} = V_{IH}$; $t_{RC} = t_{RC\text{ min}}$)	TC51V18165CJ/CFT-50	-	225	mA	3, 5
		TC51V18165CJ/CFT-60	-	185		
I _{CC4}	HYPER PAGE MODE CURRENT Average Power Supply Current, Hyper Page Mode ($\overline{\text{RAS}} = V_{IL}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$, Address Cycling: $t_{HPC} = t_{HPC\text{ min}}$)	TC51V18165CJ/CFT-50	-	145	mA	3, 4, 5
		TC51V18165CJ/CFT-60	-	125		
I _{CC5}	STANDBY CURRENT Power Supply Standby Current ($\overline{\text{RAS}} = \overline{\text{UCAS}} = \overline{\text{LCAS}} = V_{CC} - 0.2\text{ V}$)		-	500	μA	
I _{CC6}	$\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ REFRESH CURRENT Average Power Supply Current, $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Mode ($\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$ Cycling: $t_{RC} = t_{RC\text{ min}}$)	TC51V18165CJ/CFT-50	-	225	mA	3, 5
		TC51V18165CJ/CFT-60	-	185		
I _{I (L)}	INPUT LEAKAGE CURRENT Input Leakage Current, any input ($0\text{ V} \leq V_{IN} \leq V_{CC}$, All Other Pins Not under Test = 0 V)		- 10	10	μA	
I _{O (L)}	OUTPUT LEAKAGE CURRENT (D_{OUT} Is disabled, $0\text{ V} \leq V_{OUT} \leq V_{CC}$)		- 10	10	μA	
V _{OH}	OUTPUT LEVEL Output H Level Voltage ($I_{OUT} = -2\text{ mA}$)		2.4	-	V	
V _{OL}	OUTPUT LEVEL Output L Level Voltage ($I_{OUT} = 2\text{ mA}$)		-	0.4	V	

AC CHARACTERISTICS AND RECOMMENDED OPERATING CONDITIONS

($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ$ to 70°C) (Notes 6, 7, 8)

SYMBOL	PARAMETER	TC51V18165CJ/CFT				UNIT	NOTES
		-50		-60			
		MIN	MAX	MIN	MAX		
t_{RC}	Random Read or Write Cycle Time	84	-	104	-	ns	
t_{RMW}	Read-Modify-Write Cycle Time	111	-	135	-	ns	
t_{RAC}	Access Time from \overline{RAS}	-	50	-	60	ns	9,14,15
t_{CAC}	Access Time from \overline{CAS}	-	14	-	17	ns	9,14
t_{AA}	Access Time from Column Address	-	25	-	30	ns	9,15
t_{CPA}	Access Time from \overline{CAS} Precharge	-	28	-	35	ns	9
t_{CLZ}	\overline{CAS} to output in Low-Z	0	-	0	-	ns	
t_{OFF}	Output Buffer Turn-off Delay	0	13	0	15	ns	10,16
t_T	Transition Time (Rise and Fall)	1	50	1	50	ns	8
t_{RP}	\overline{RAS} Precharge Time	30	-	40	-	ns	
t_{RAS}	\overline{RAS} Pulse Width	50	10,000	60	10,000	ns	
t_{RASP}	\overline{RAS} Pulse Width (Hyper Page Mode)	50	100,000	60	100,000	ns	
t_{RSH}	\overline{RAS} Hold Time	8	-	10	-	ns	
t_{RHCP}	\overline{RAS} Hold Time From \overline{CAS} Precharge (Hyper Page Mode)	28	-	35	-	ns	
t_{CSH}	\overline{CAS} Hold Time	35	-	40	-	ns	
t_{CAS}	\overline{CAS} Pulse Width	8	10,000	10	10,000	ns	
t_{RCD}	\overline{RAS} -to- \overline{CAS} Delay Time	12	36	14	43	ns	14
t_{RAD}	\overline{RAS} -to-Column-Address Delay Time	10	25	12	30	ns	15
t_{CRP}	\overline{CAS} -to- \overline{RAS} Precharge Time	5	-	5	-	ns	
t_{CP}	\overline{CAS} Precharge Time	8	-	10	-	ns	
t_{ASR}	Row Address Set up Time	0	-	0	-	ns	
t_{RAH}	Row Address Hold Time	8	-	10	-	ns	
t_{ASC}	Column Address Set up Time	0	-	0	-	ns	
t_{CAH}	Column Address Hold Time	8	-	10	-	ns	
t_{RAL}	Column-Address-to- \overline{RAS} Lead Time	25	-	30	-	ns	
t_{RCS}	Read Command Set up Time Referenced to \overline{RAS}	0	-	0	-	ns	
t_{RCH}	Read Command Hold Time	0	-	0	-	ns	11
t_{RRH}	Read Command Hold Time Referenced to \overline{RAS}	0	-	0	-	ns	11
t_{WCH}	Write Command Hold Time	8	-	10	-	ns	

AC CHARACTERISTICS AND RECOMMENDED OPERATING CONDITIONS (Continued)

SYMBOL	PARAMETER	TC51V18165CJ/CFT				UNIT	NOTES
		-50		-60			
		MIN	MAX	MIN	MAX		
t _{WP}	Write Command Pulse Width	8	–	10	–	ns	
t _{RWL}	Write-Command-to- $\overline{\text{RAS}}$ Lead Time	8	–	10	–	ns	
t _{CWL}	Write-Command-to- $\overline{\text{CAS}}$ Lead Time	8	–	10	–	ns	
t _{DS}	Data Set up Time	0	–	0	–	ns	12
t _{DH}	Data Hold Time	8	–	10	–	ns	12
t _{REF}	Refresh Period	–	16	–	16	ms	
t _{WCS}	Write Command Set up Time	0	–	0	–	ns	13
t _{CWD}	$\overline{\text{CAS}}$ -to- $\overline{\text{WE}}$ Delay Time	31	–	36	–	ns	13
t _{RWD}	$\overline{\text{RAS}}$ -to- $\overline{\text{WE}}$ Delay Time	67	–	79	–	ns	13
t _{AWD}	Column-Address-to- $\overline{\text{WE}}$ Delay Time	42	–	49	–	ns	13
t _{CPWD}	$\overline{\text{CAS}}$ -Precharge-to- $\overline{\text{WE}}$ Delay Time	45	–	54	–	ns	13
t _{CSR}	$\overline{\text{CAS}}$ Set up Time ($\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Cycle)	5	–	5	–	ns	
t _{CHR}	$\overline{\text{CAS}}$ Hold Time ($\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Cycle)	8	–	10	–	ns	
t _{RPC}	$\overline{\text{RAS}}$ -to- $\overline{\text{CAS}}$ Precharge Time	5	–	5	–	ns	
t _{CPT}	$\overline{\text{CAS}}$ Precharge Time ($\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Counter Test Cycle)	20	–	20	–	ns	
t _{ROH}	$\overline{\text{RAS}}$ Hold Time Referenced to $\overline{\text{OE}}$	8	–	10	–	ns	
t _{OEA}	$\overline{\text{OE}}$ Access Time	–	13	–	15	ns	9
t _{OED}	$\overline{\text{OE}}$ -to-Data Delay	13	–	15	–	ns	
t _{OLZ}	$\overline{\text{OE}}$ to Output in Low - Z	0	–	0	–	ns	
t _{OEZ}	Output Buffer Turn-off Delay Time from $\overline{\text{OE}}$	0	13	0	15	ns	10
t _{OEH}	$\overline{\text{OE}}$ Command Hold Time	8	–	10	–	ns	
t _{ODS}	Output Disable Set up Time	0	–	0	–	ns	

AC CHARACTERISTICS AND RECOMMENDED OPERATING CONDITIONS (Continued)

SYMBOL	PARAMETER	TC51V18165CJ/CFT				UNIT	NOTES
		-50		-60			
		MIN	MAX	MIN	MAX		
t _{RNCD}	\overline{RAS} to next \overline{CAS} Delay Time (Hyper Page Mode)	50	-	60	-	ns	
t _{HPC}	Hyper Page Mode Cycle Time	20	-	25	-	ns	
t _{HPRWC}	Hyper Page Mode Read-Modify-Write Cycle Time	57	-	68	-	ns	
t _{COH}	Output Data Hold time	5	-	5	-	ns	
t _{REZ}	Output Buffer Turn-off Delay from \overline{RAS}	0	13	0	15	ns	10,16
t _{WEZ}	Output Buffer Turn-off Delay from \overline{WE}	0	13	0	15	ns	10
t _{WED}	\overline{WE} -to-Data Delay	13	-	15	-	ns	
t _{OE}	\overline{OE} Pulse Width	13	-	15	-	ns	
t _{OEP}	\overline{OE} Precharge Time	8	-	10	-	ns	
t _{CPO}	\overline{CAS} to \overline{OE} Precharge Time	5	-	5	-	ns	
t _{OCH}	\overline{CAS} Hold Time Referenced to \overline{OE}	8	-	10	-	ns	

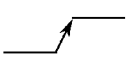
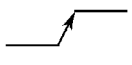

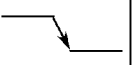
CAPACITANCE (V_{CC} = 3.3 V ± 0.3 V, f = 1 MHz, Ta = 0° to 70°C)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNIT
C ₁₁	Input Capacitance (A0 to A9)	-	5	pF
C ₁₂	Input Capacitance (\overline{RAS} , \overline{UCAS} , \overline{LCAS} , \overline{WE} , \overline{OE})	-	7	pF
C _O	I/O Capacitance (I/O1 to I/O16)	-	7	pF



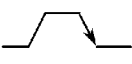
NOTES:

1. Conditions outside the limits listed under “Absolute Maximum Rating” may cause permanent damage to the device.
2. All voltages are referenced to V_{SS} .
3. I_{CC1} , I_{CC3} , I_{CC4} , I_{CC6} depend on cycle rate.
4. I_{CC1} , I_{CC4} depend on output loading. Specified values are obtained with the output open.
5. Address can be changed once at most while $\overline{RAS} = V_{IL}$. In case of I_{CC4} , it can be changed once at most during a Hyper Page mode cycle (t_{HPC}).
6. An initial pause of 200 μs is required after power-up followed by 8 \overline{RAS} -Only refresh cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 \overline{CAS} -before- \overline{RAS} refresh cycles instead of 8 \overline{RAS} -Only refresh cycles are required.
7. AC measurements assume $t_T = 2$ ns.
8. V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} and V_{IL} .
9. This is measured with a load equivalent to 1 TTL load and 100 pF at $V_{OH} = 2.0$ V ($I_{OUT} = -2$ mA), $V_{OL} = 0.8$ V ($I_{OUT} = 2$ mA).
10. t_{OFF} (max), t_{OEZ} (max), t_{REZ} (max) and t_{WEZ} (max) define the time at which the output goes open circuit and are not referenced to output voltage levels.
11. Either t_{RCH} or t_{RRH} must be satisfied for a Read cycle.
12. These parameters are referenced to \overline{UCAS} , \overline{LCAS} leading edge of \overline{CAS} in Early Write cycles and to leading edge of \overline{WE} in Read-Modify-Write cycles.
13. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}(\text{min})$, the cycle is an Early Write cycle and the data out pin will remain open circuit (high impedance) through the entire cycle; If $t_{RWD} \geq t_{RWD}(\text{min})$, $t_{CWD} \geq t_{CWD}(\text{min})$, $t_{AWD} \geq t_{AWD}(\text{min})$ and $t_{CPWD} \geq t_{CPWD}(\text{min})$ (Hyper Page mode), the cycle is a Read-Modify-Write cycle and the data out will contain data read from the selected cell; If neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
14. Operation within the $t_{RCD}(\text{max})$ limit ensures that $t_{RAC}(\text{max})$ can be met.
 $t_{RCD}(\text{max})$ is specified as a reference point only: If t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, then access time is determined by t_{CAC} .
15. Operation within the $t_{RAD}(\text{max})$ limit ensures that $t_{RAC}(\text{max})$ can be met.
 $t_{RAD}(\text{max})$ is specified as a reference point only: If t_{RAD} is greater than the specified $t_{RAD}(\text{max})$ limit, then access time is determined by t_{AA} .
16. If \overline{RAS} goes to high before \overline{CAS} high going, the open circuit condition of the output is achieved by \overline{CAS} high going (t_{OFF}). If \overline{CAS} goes to high before \overline{RAS} high going, the open circuit condition of the output is achieved by \overline{RAS} high going (t_{REZ}).

DATA-OUT LO-Z CONTROL LOGIC

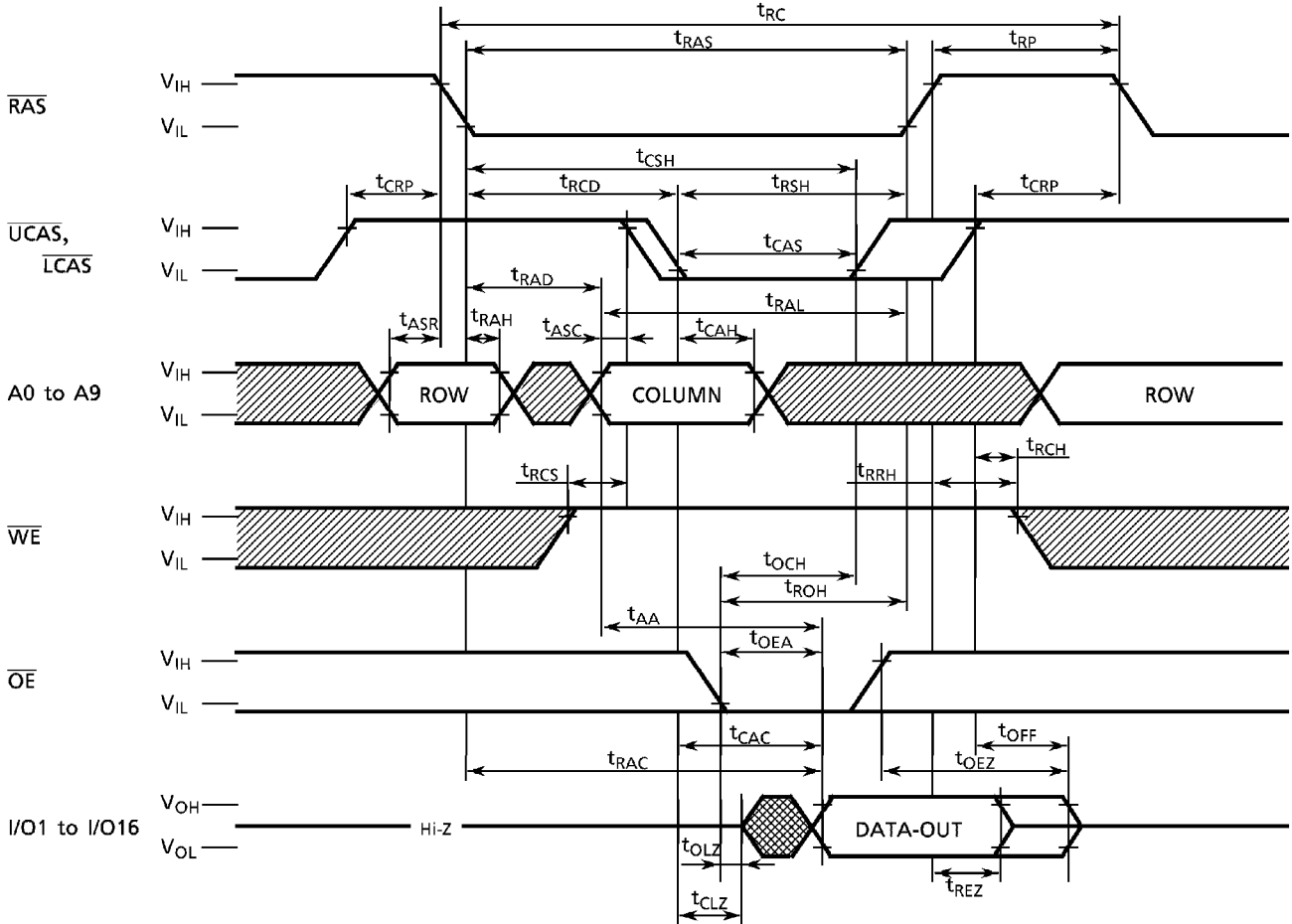
$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	Timing Specification
H		L	H	t_{OFF}
	H	L	H	t_{REZ}
L	L		H	t_{OEZ}
L	H	L		t_{WEZ}

DATA-OUT LO-Z CONTROL LOGIC



$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	Timing Specification
L		L	H	t_{CLZ}
L	L		H	t_{OLZ}
L	L		H	t_{OLZ}

TIMING DIAGRAMS

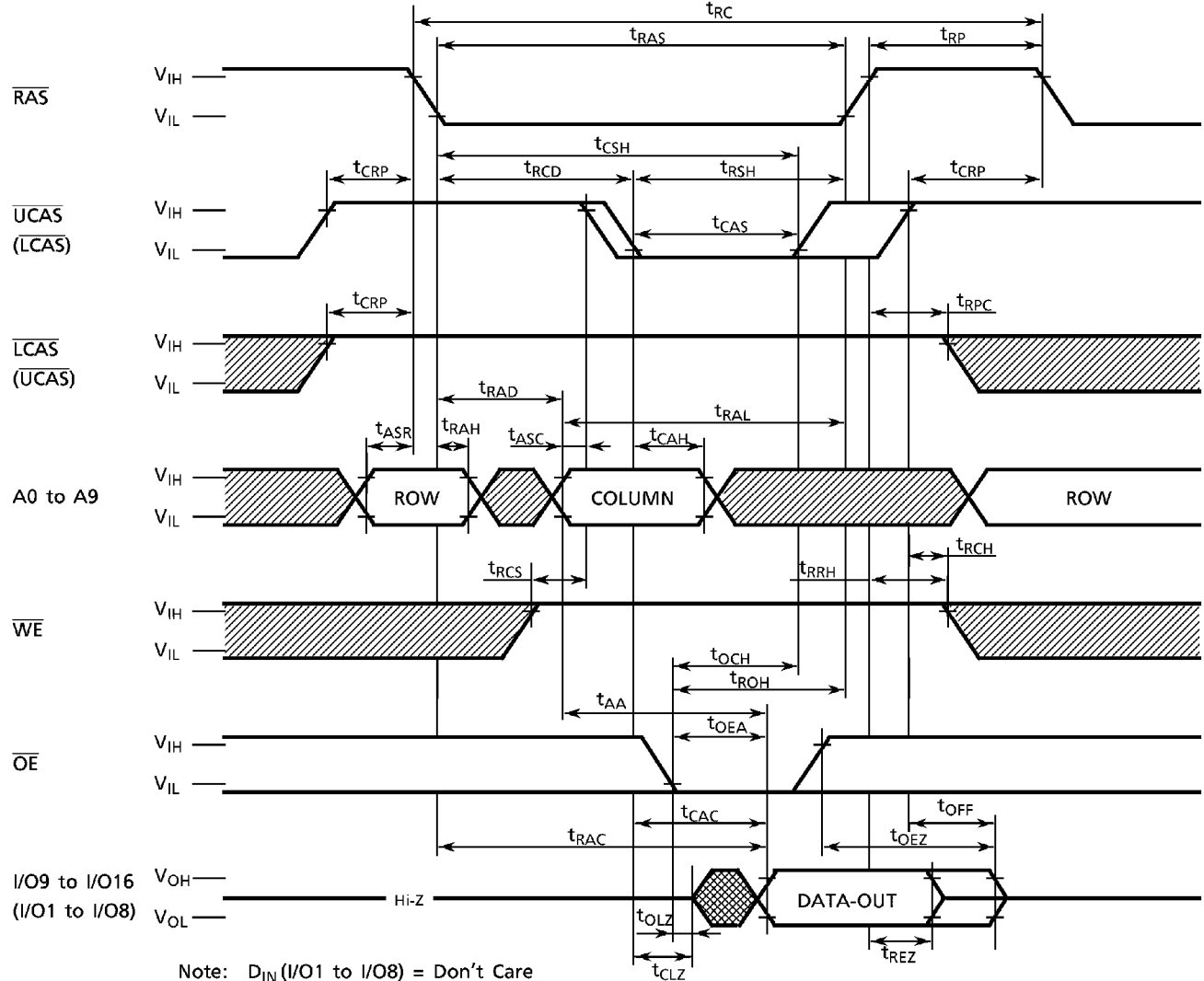
READ CYCLE





Note: $D_{IN} = Hi-Z$

 : H or L
 : Invalid Data

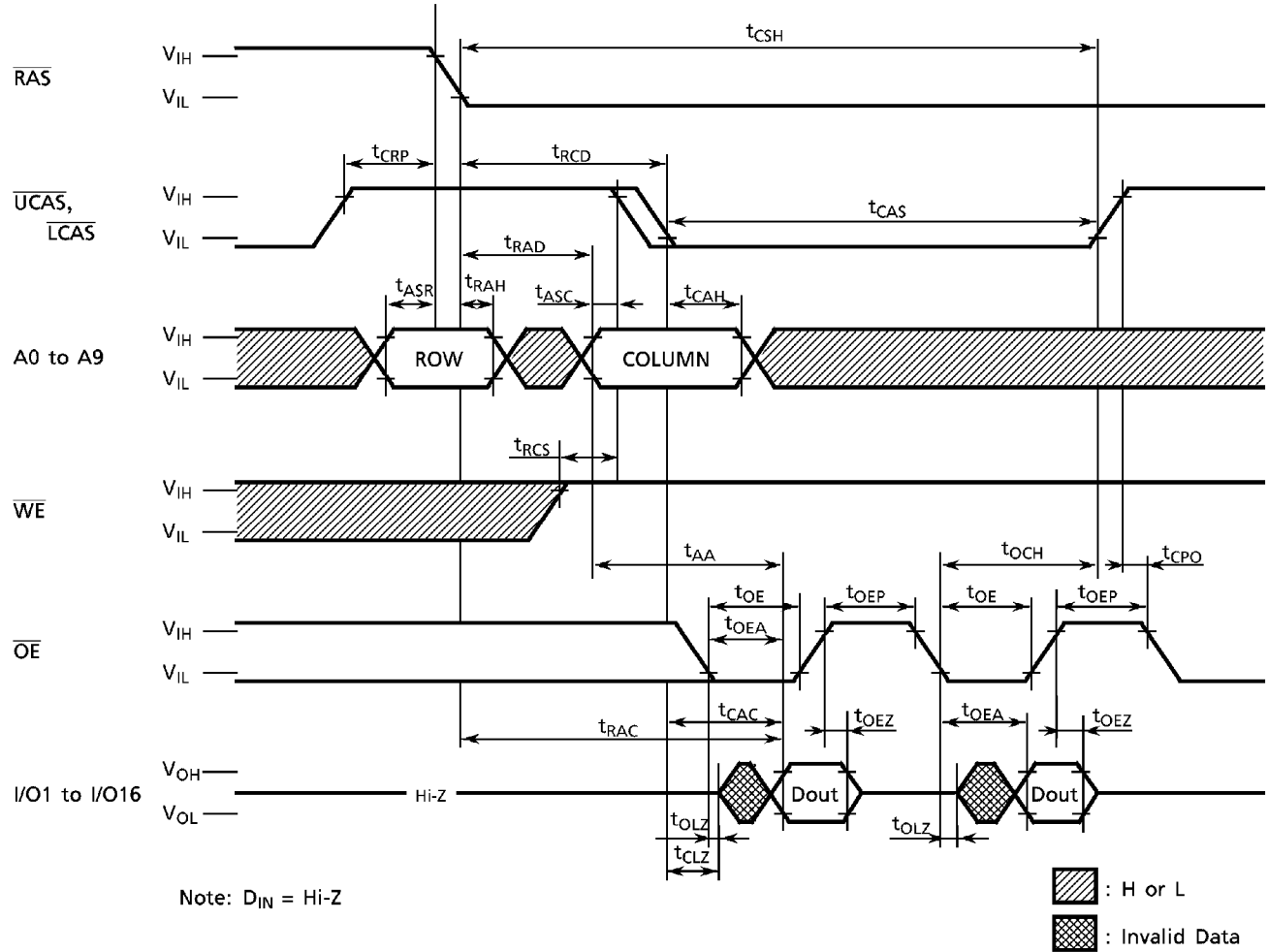
BYTE READ CYCLE



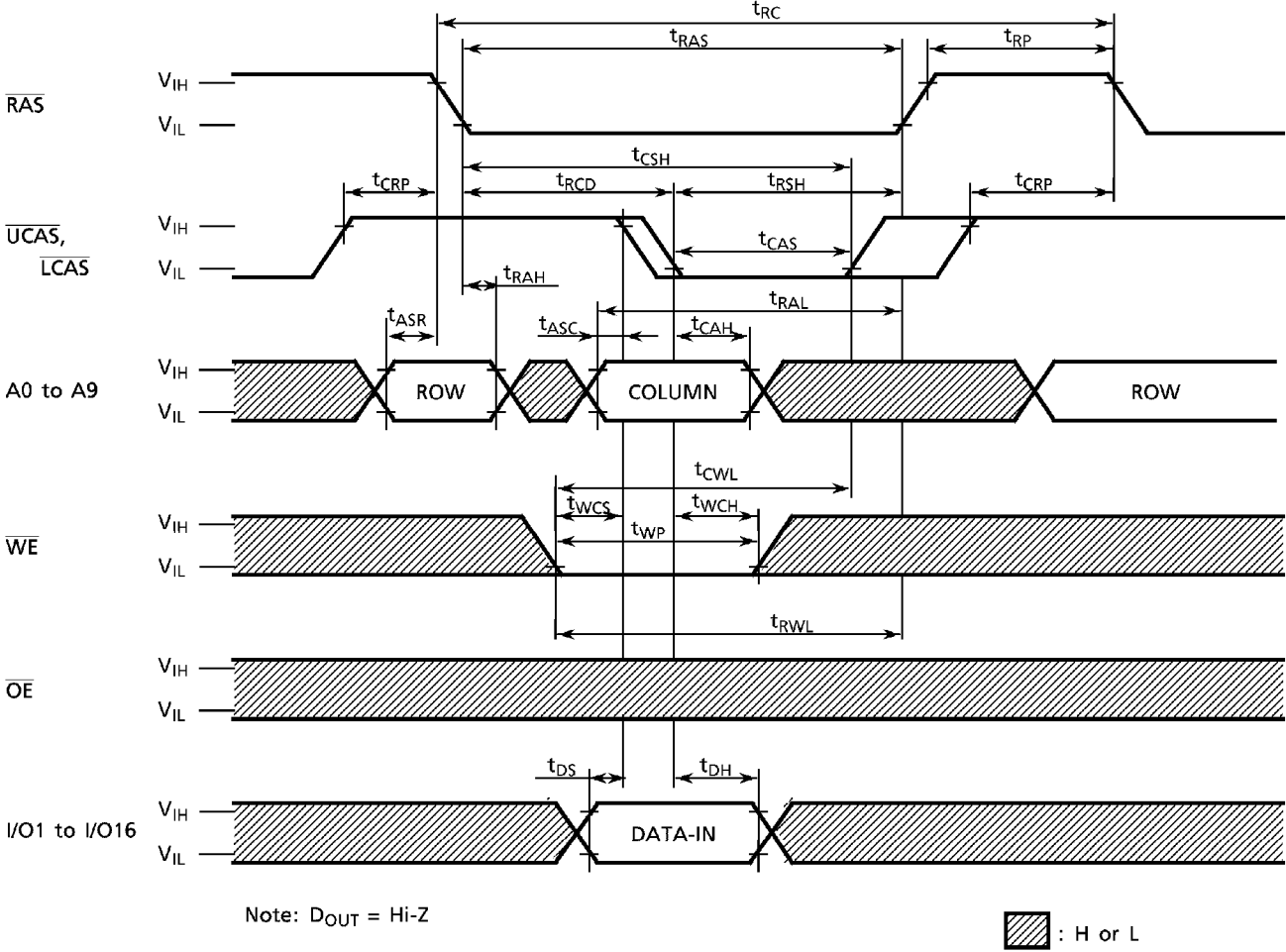
Note: $D_{IN}(I/O1 \text{ to } I/O8) = \text{Don't Care}$
 $D_{IN}(I/O9 \text{ to } I/O16) = \text{Hi-Z}$
 $D_{OUT}(I/O1 \text{ to } I/O8) = \text{Hi-Z}$
 $D_{IN}(I/O9 \text{ to } I/O16) = \text{Don't Care}$
 $D_{IN}(I/O1 \text{ to } I/O8) = \text{Hi-Z}$
 $D_{OUT}(I/O9 \text{ to } I/O16) = \text{Hi-Z}$

 : H or L
 : Invalid Data

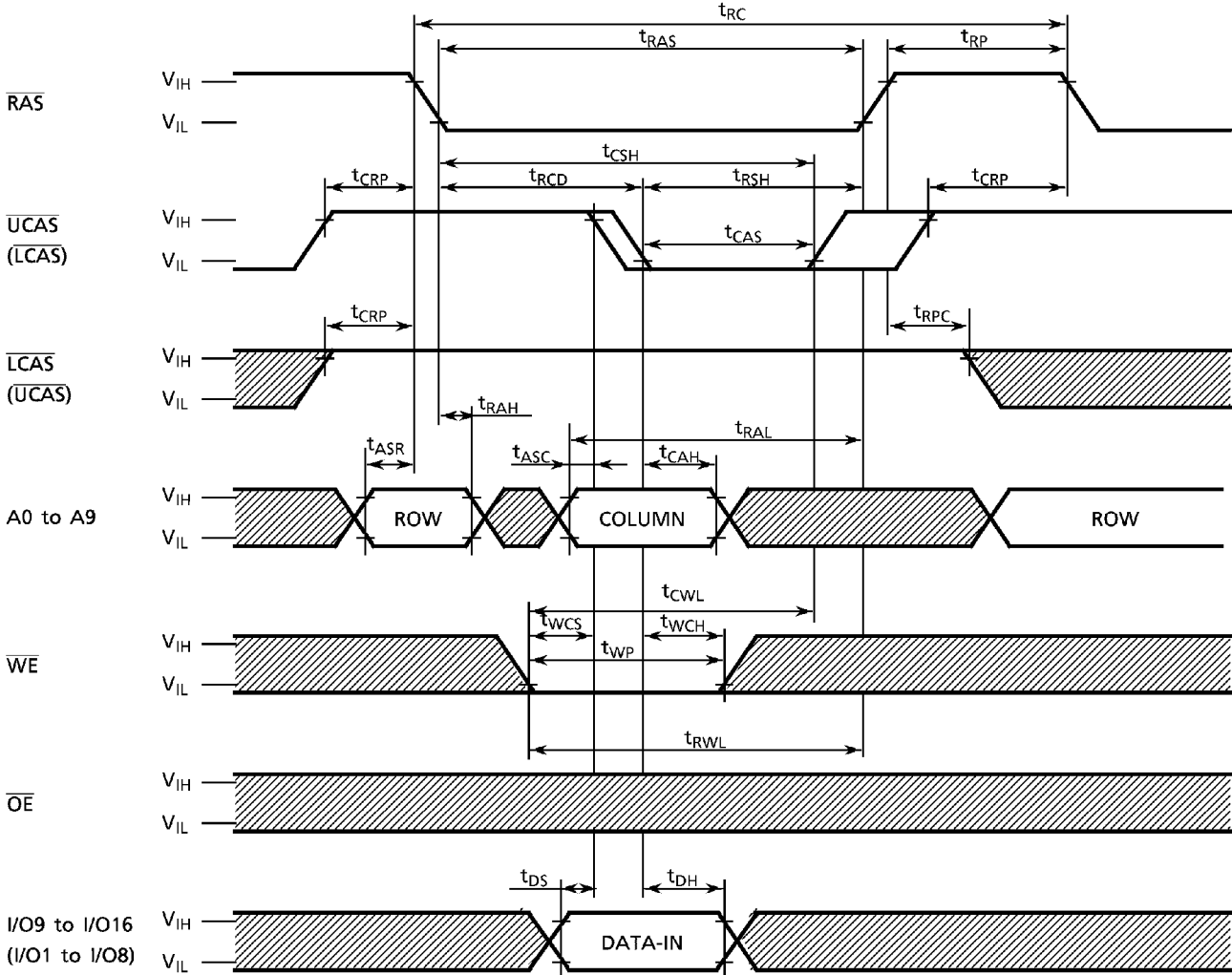
OE-CONTROLLED READ CYCLE



WRITE CYCLE (EARLY WRITE)



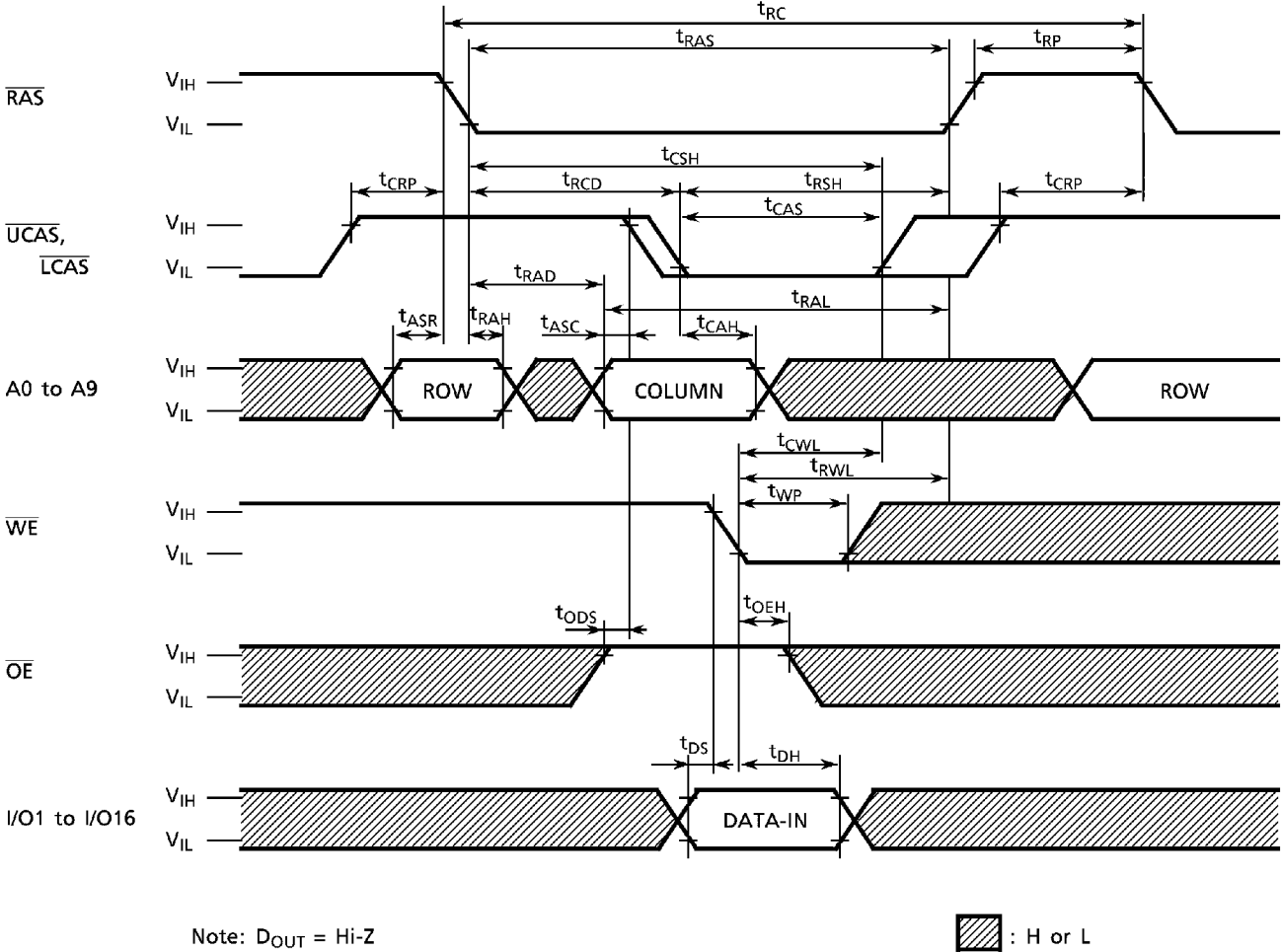
BYTE WRITE CYCLE (EARLY WRITE)



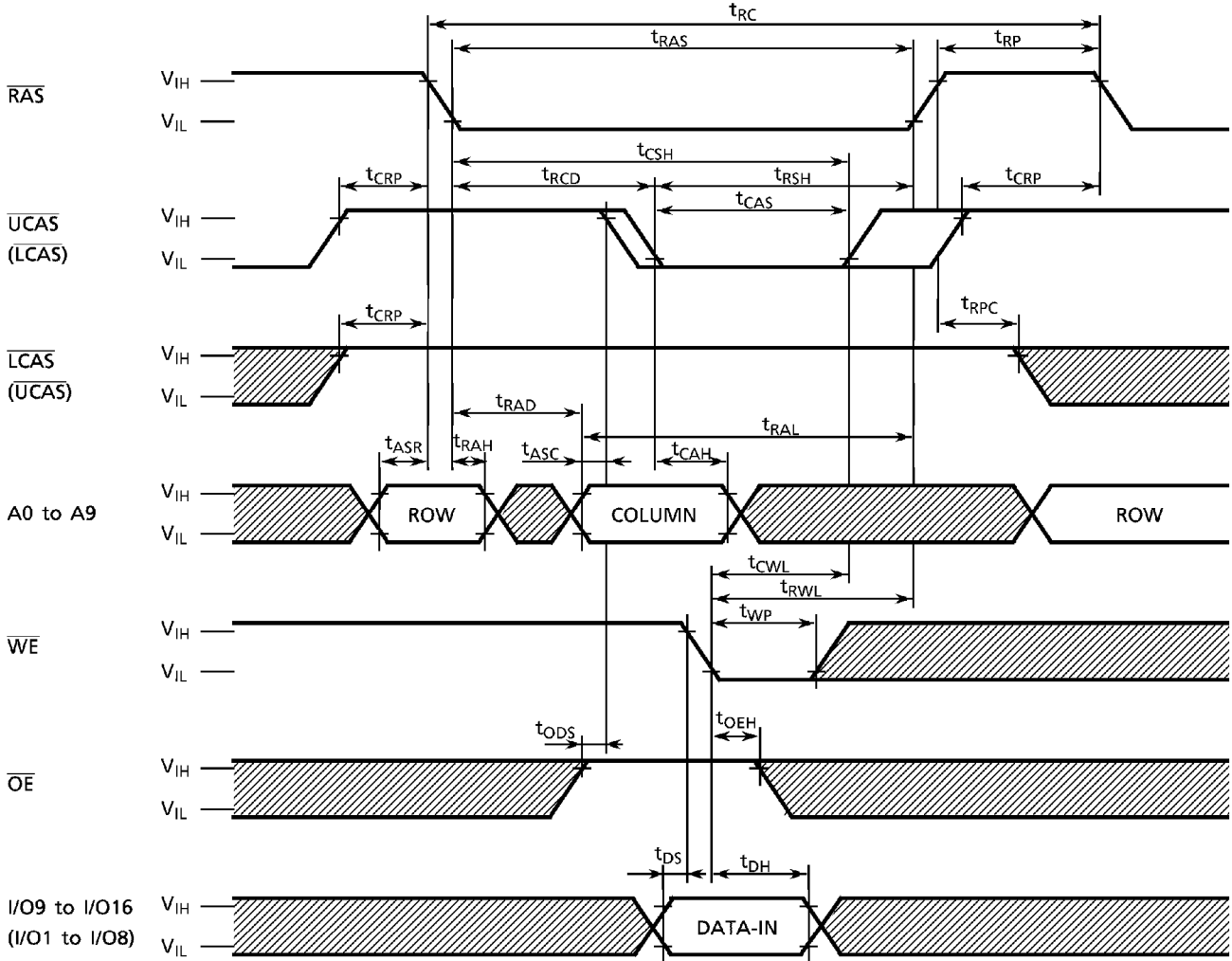
Note: D_{IN} (I/O1 to I/O8) = Don't Care
 D_{IN} (I/O9 to I/O16) = Don't Care
 D_{OUT} = Hi-Z

▨ : H or L

OE-CONTROLLED WRITE CYCLE



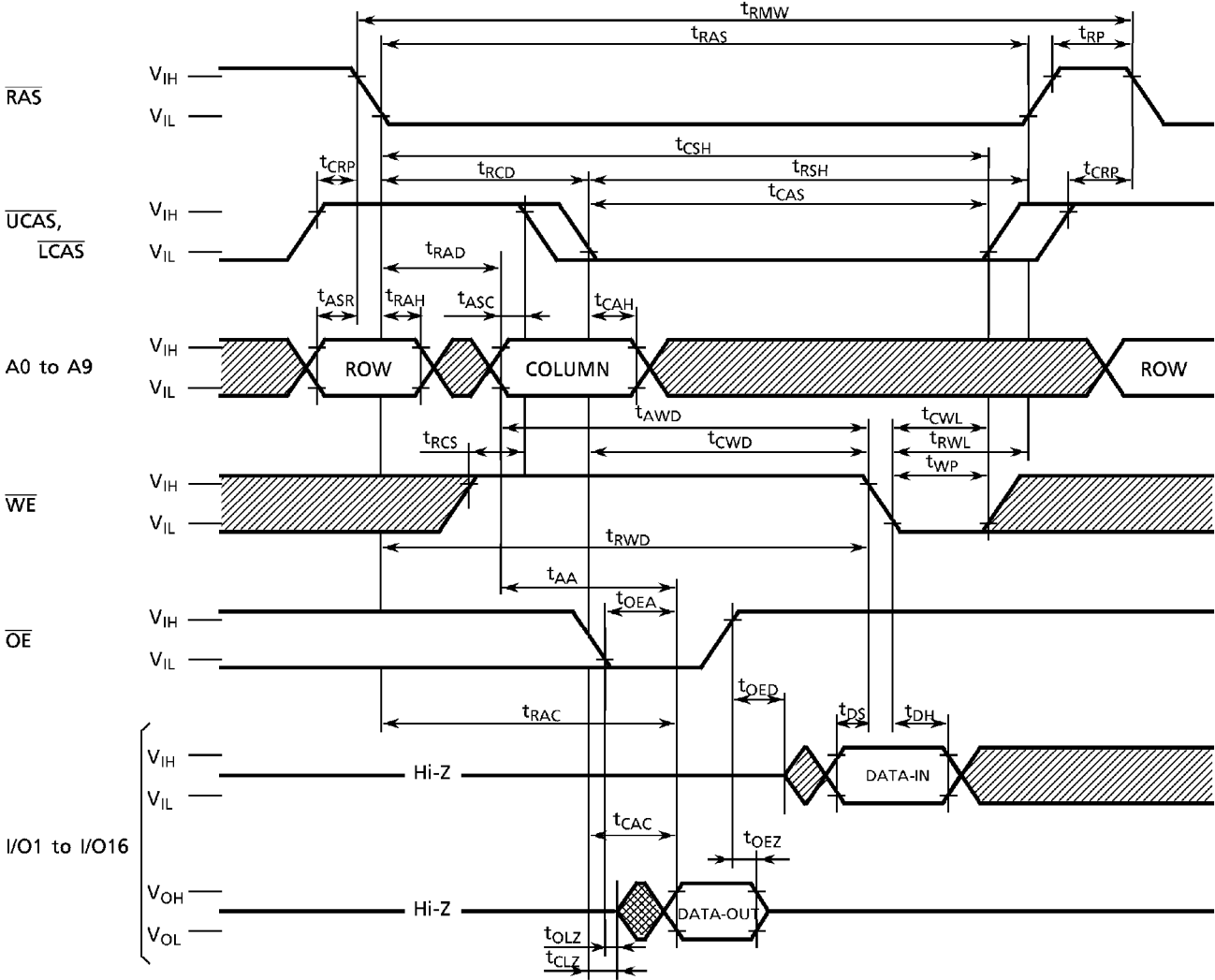
OE-CONTROLLED BYTE WRITE CYCLE



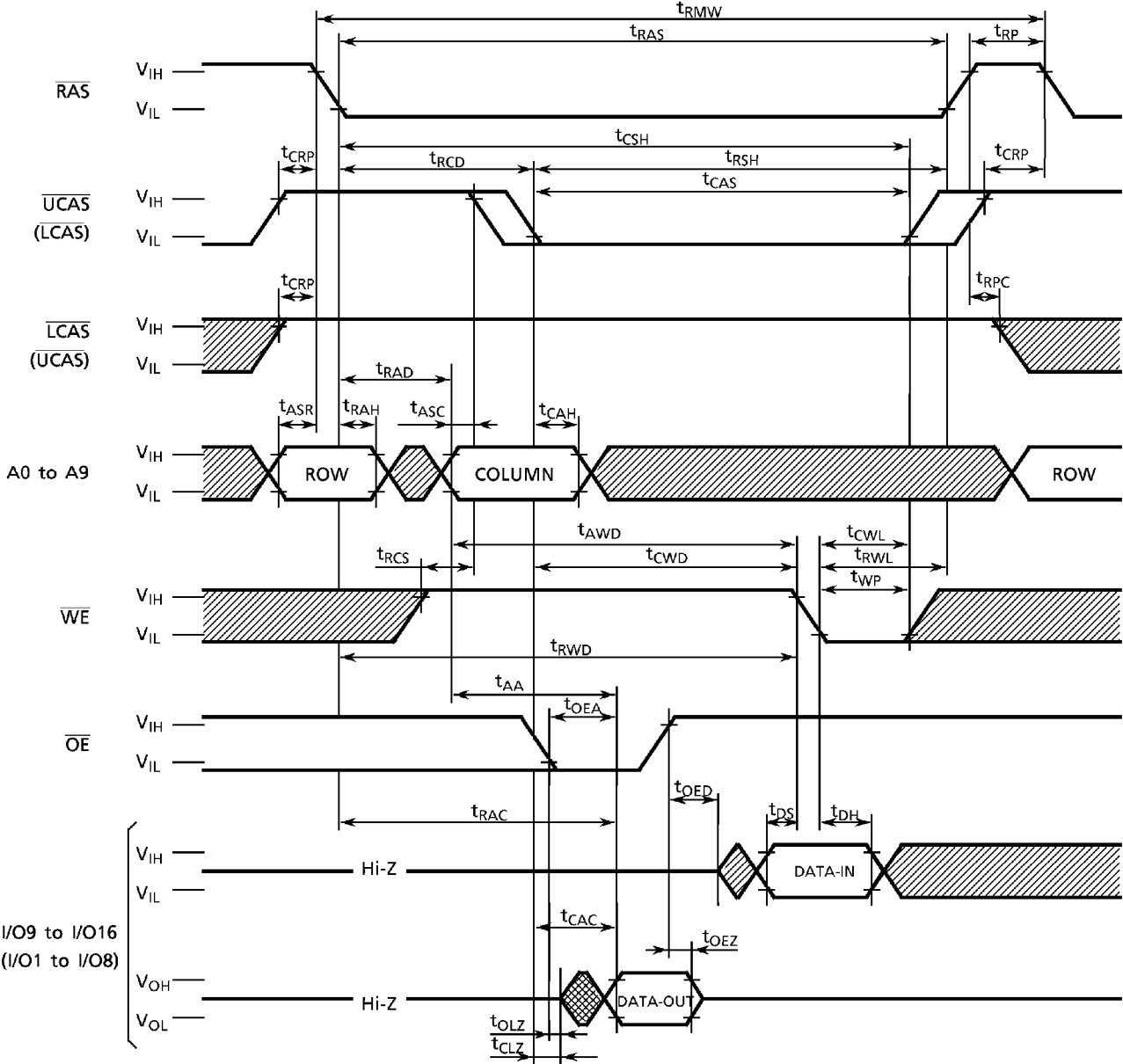
Note: D_{IN} (I/O1 to I/O8) = Don't Care
 D_{IN} (I/O9 to I/O16) = Don't Care
 D_{OUT} = Hi-Z

▨ : H or L

READ-MODIFY-WRITE CYCLE



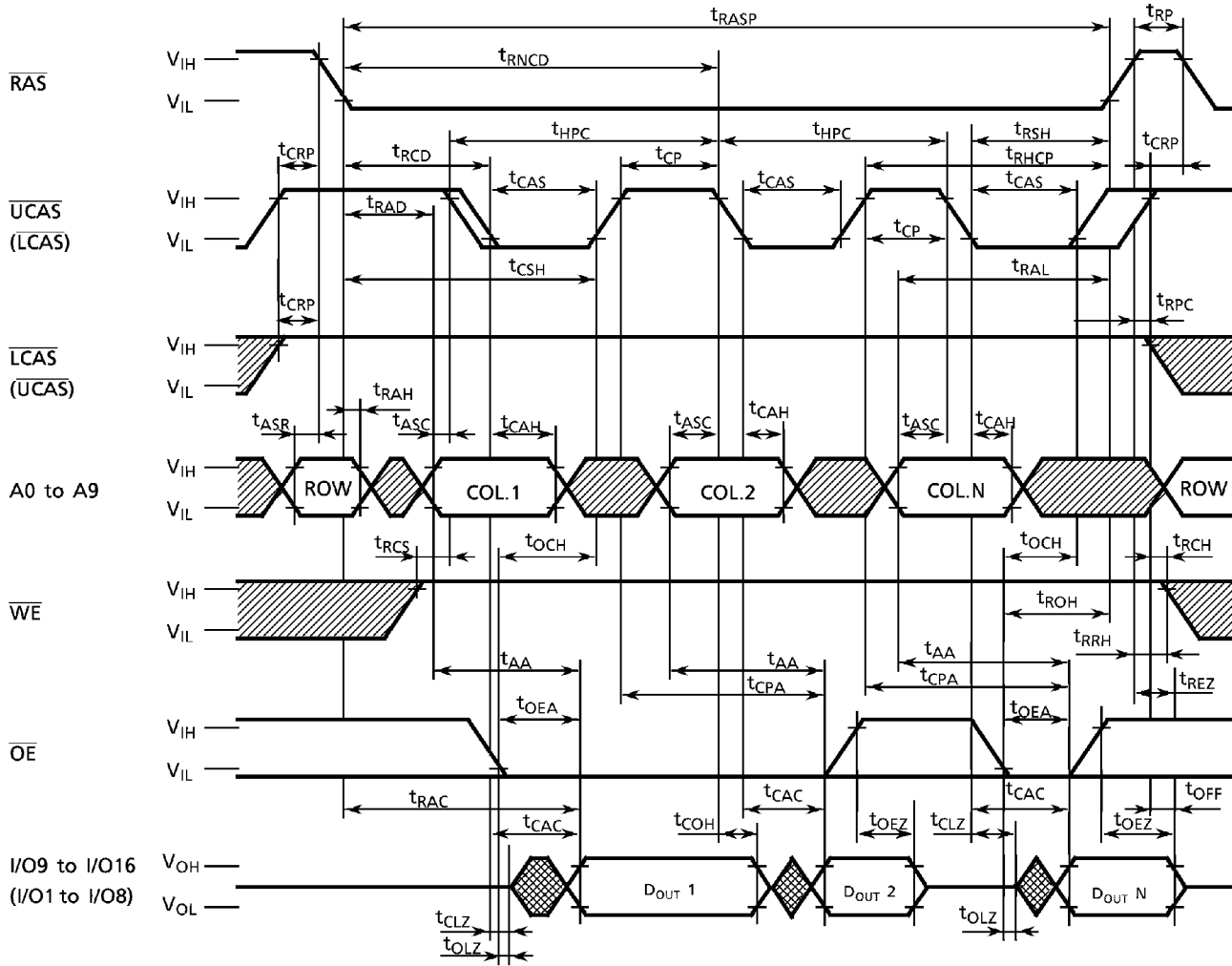
BYTE READ-MODIFY-WRITE CYCLE





Note: D_{IN} (I/O1 to I/O8) = Don't Care
 D_{OUT} (I/O1 to I/O8) = Hi-Z
 (D_{IN} (I/O9 to I/O16) = Don't Care)
 D_{OUT} (I/O9 to I/O16) = Hi-Z

▨ : H or L
 ▩ : Invalid Data

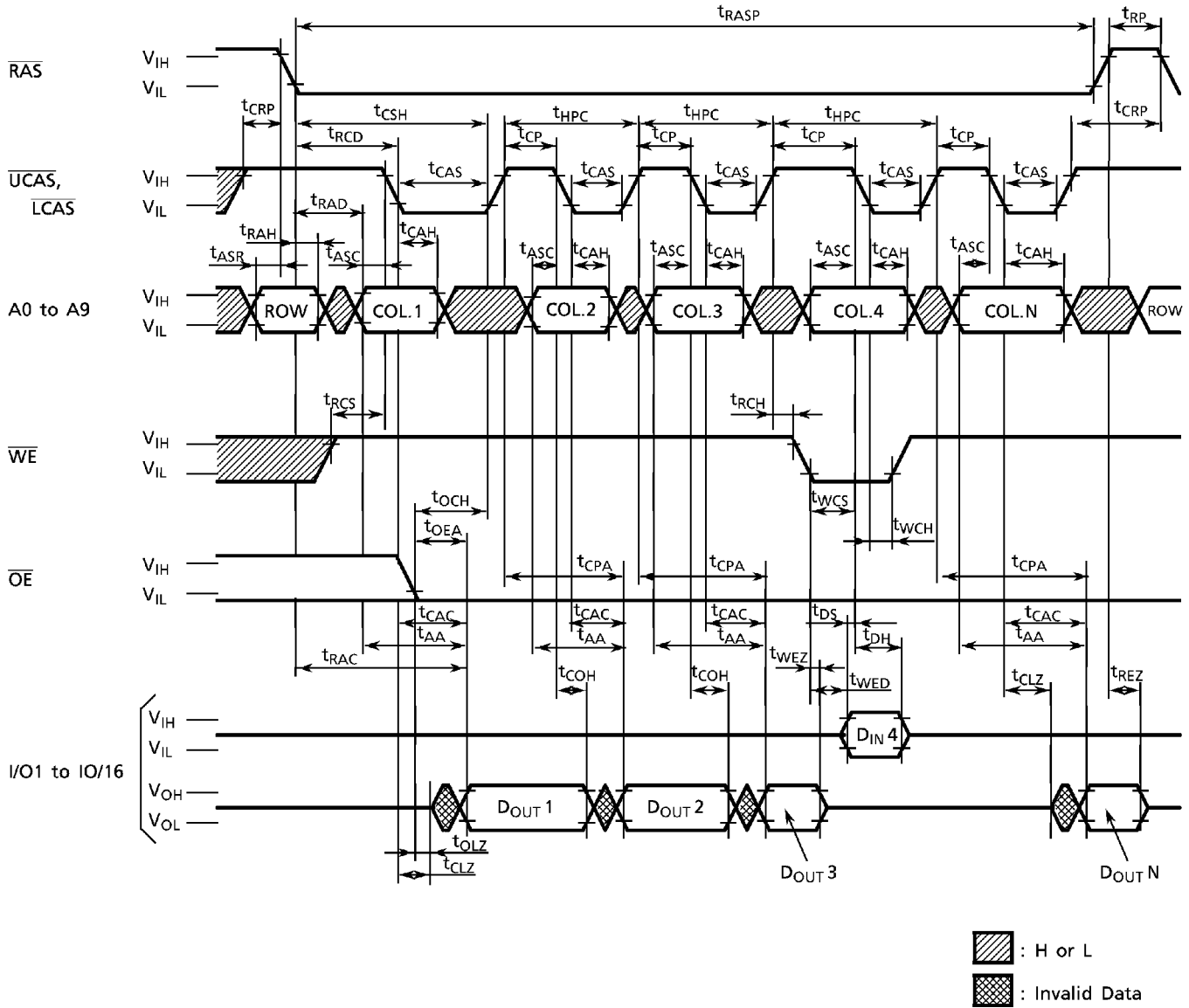
HYPER PAGE MODE BYTE READ CYCLE



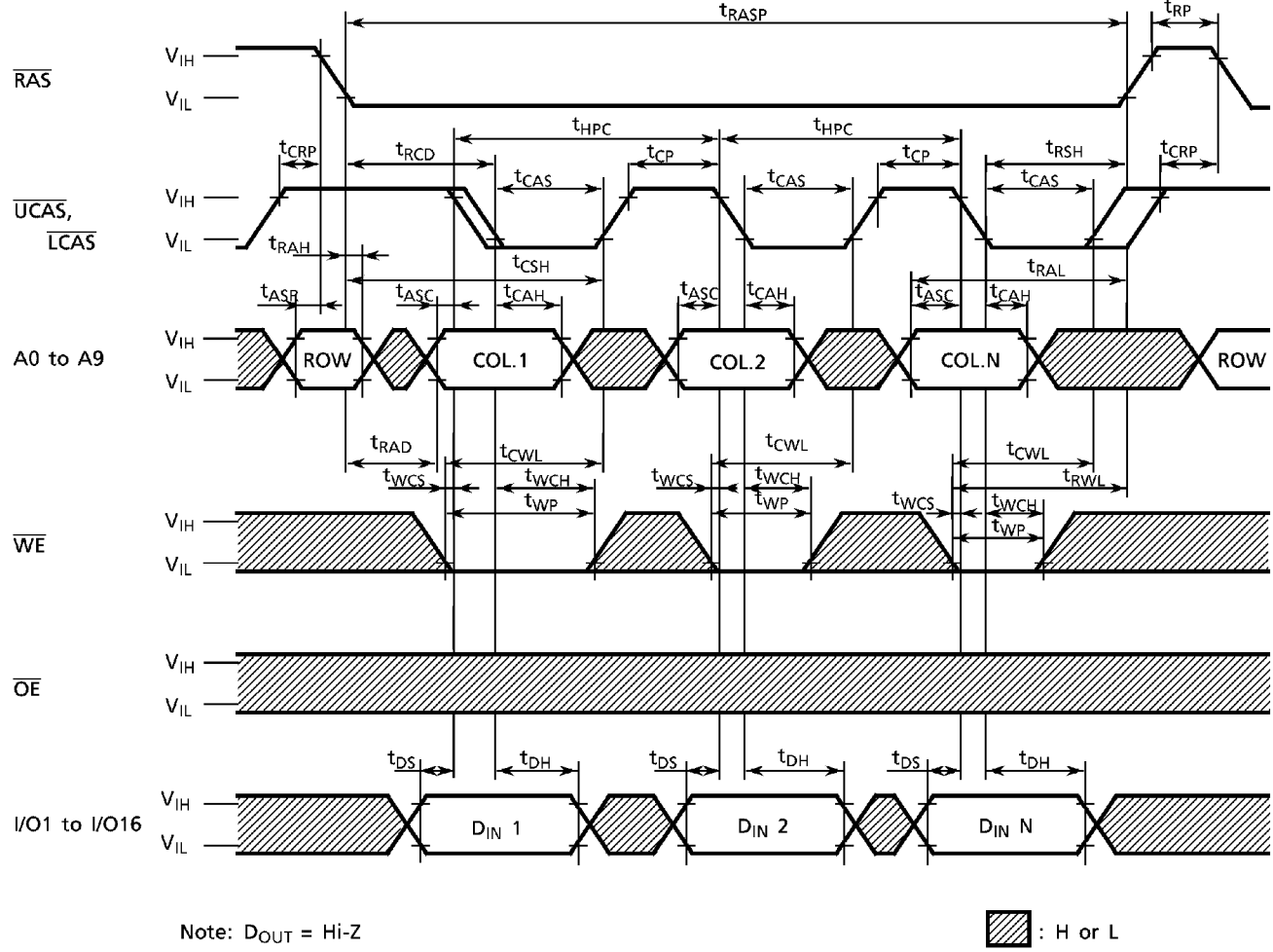
Note : D_{IN} (I/O1 to I/O8) = Don't Care
 D_{OUT} (I/O1 to I/O8) = Hi-Z
 (D_{IN} (I/O9 to I/O16) = Don't Care)
 (D_{OUT} (I/O9 to I/O16) = Hi-Z)

 : H or L
 : Invalid Data

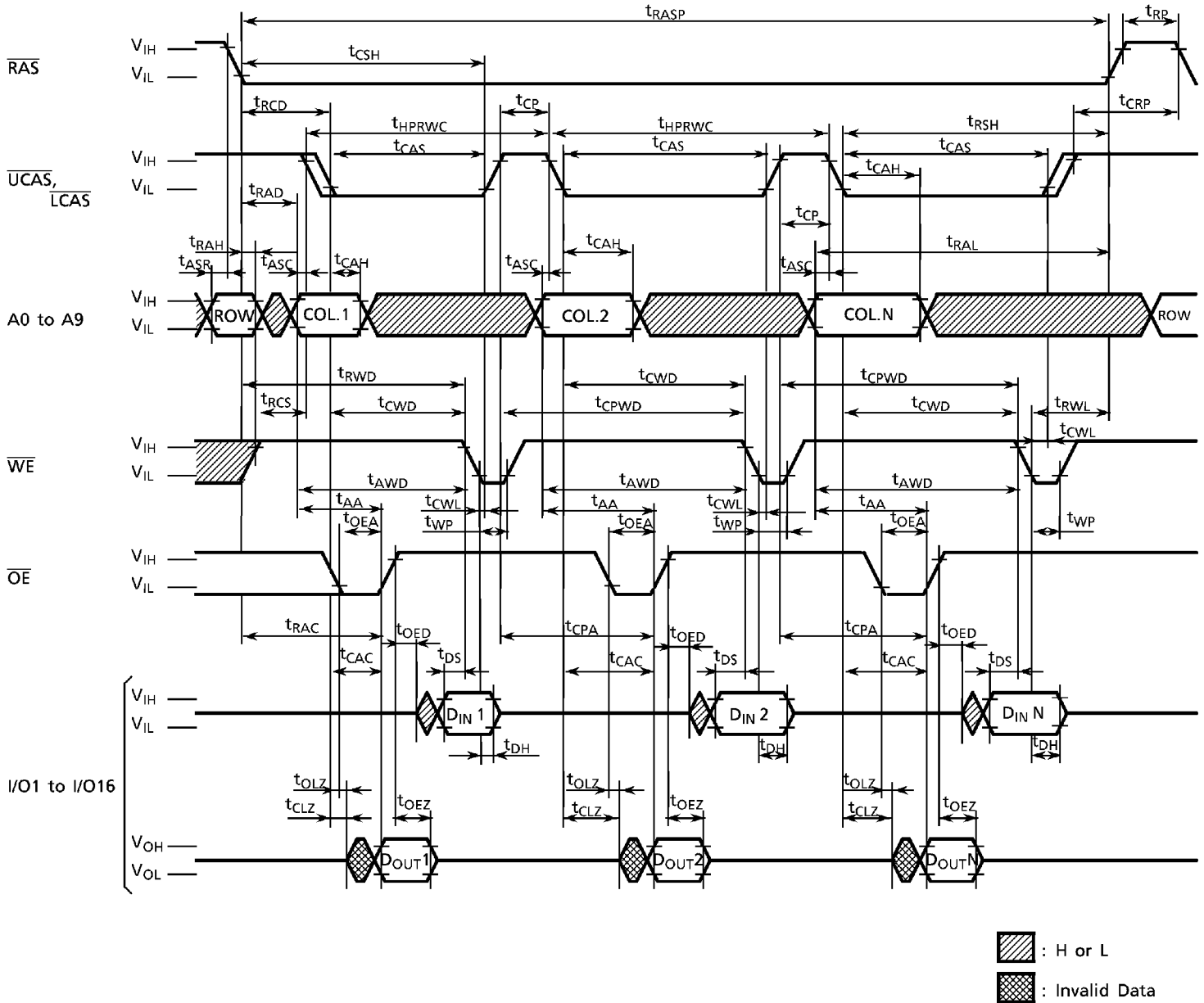
HYPER PAGE MODE READ-WRITE MIXED CYCLE



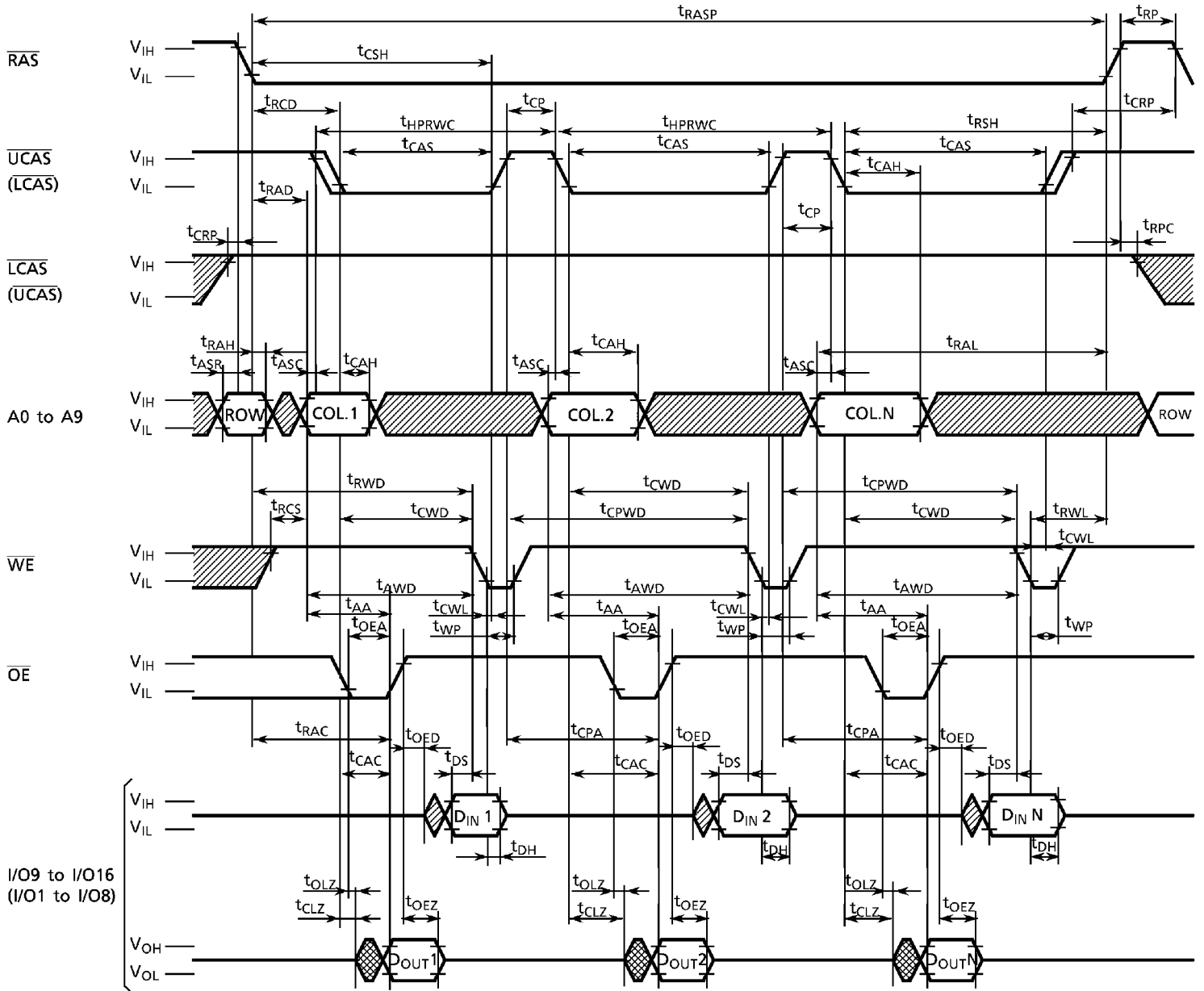
HYPER PAGE MODE WRITE CYCLE (EARLY WRITE)



HYPER PAGE MODE READ-MODIFY-WRITE CYCLE



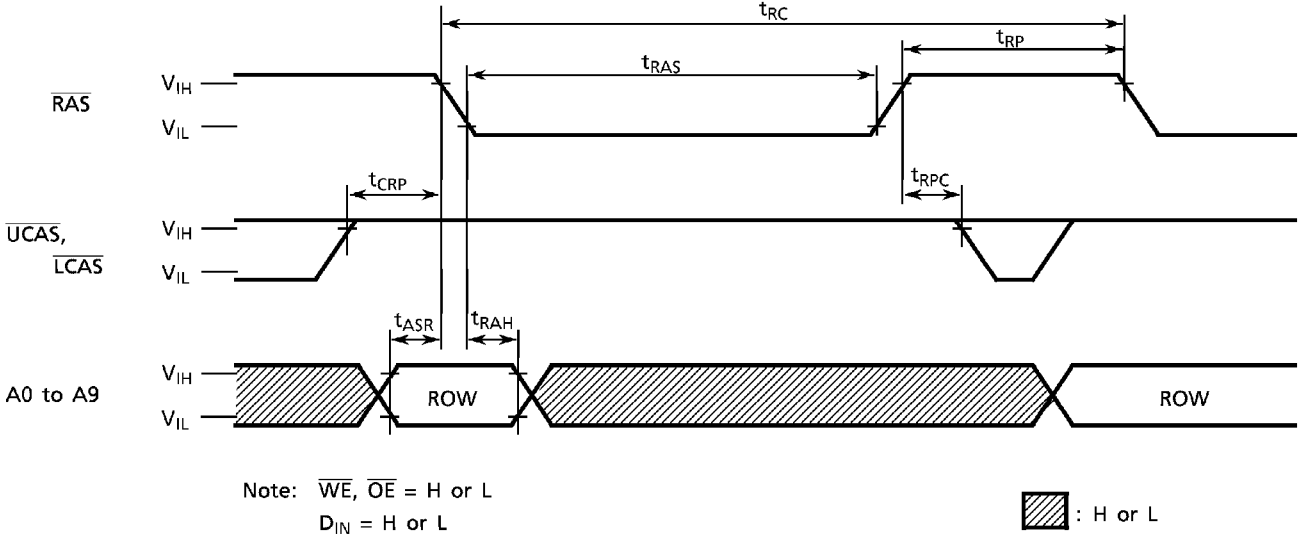
HYPER PAGE MODE BYTE READ-MODIFY-WRITE CYCLE



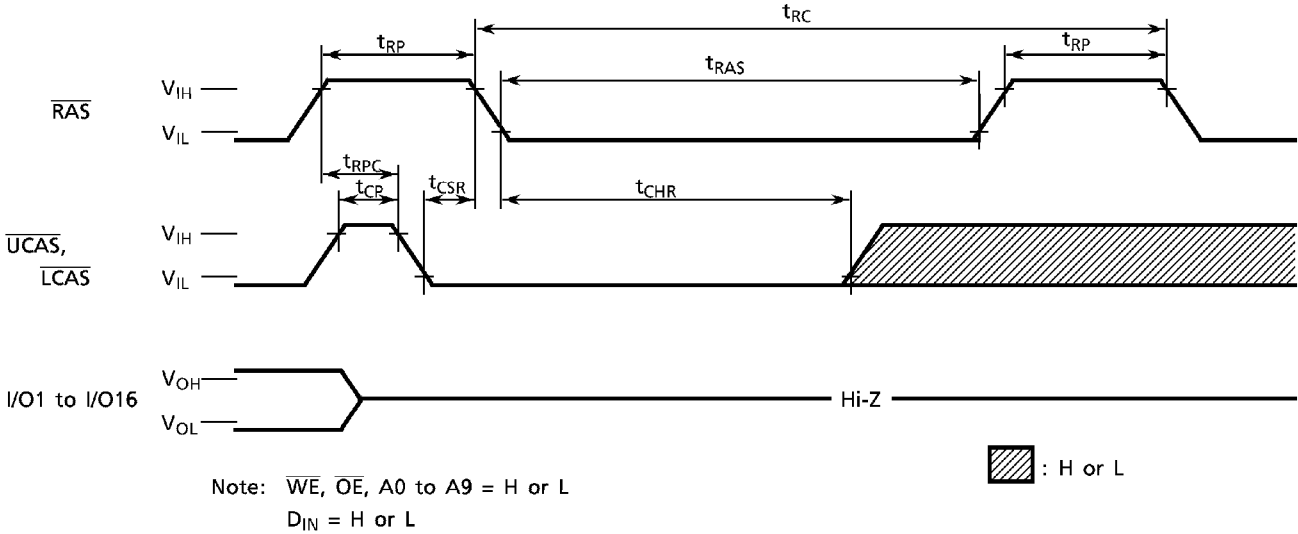
Note: D_{IN} (I/O1 to I/O8) = Don't Care
 D_{OUT} (I/O1 to I/O8) = Hi-Z
 (D_{IN} (I/O9 to I/O16) = Don't Care)
 (D_{OUT} (I/O9 to I/O16) = Hi-Z)

▨ : H or L
 ▩ : Invalid Data

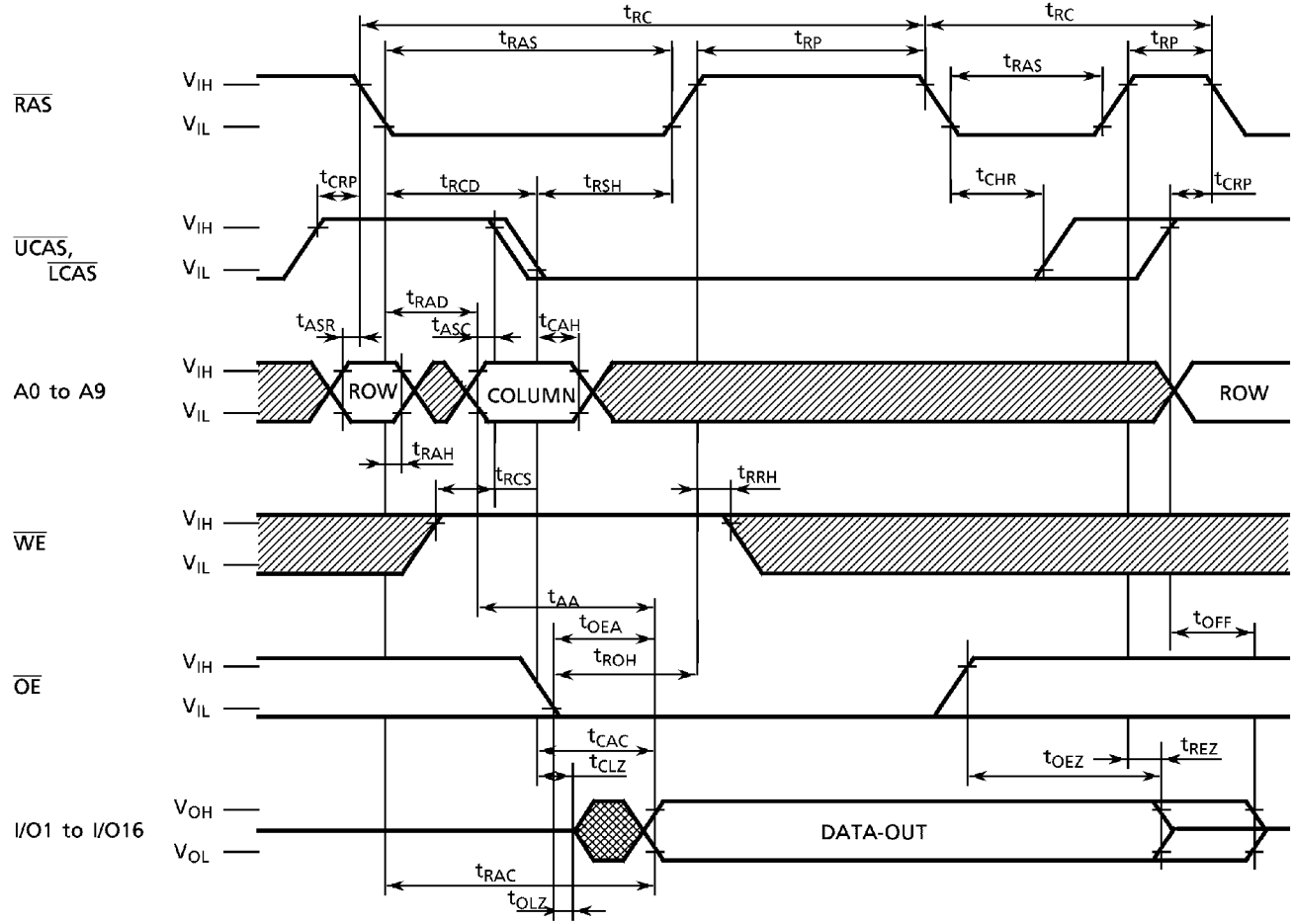
RAS-ONLY REFRESH CYCLE





CAS-BEFORE-RAS REFRESH CYCLE



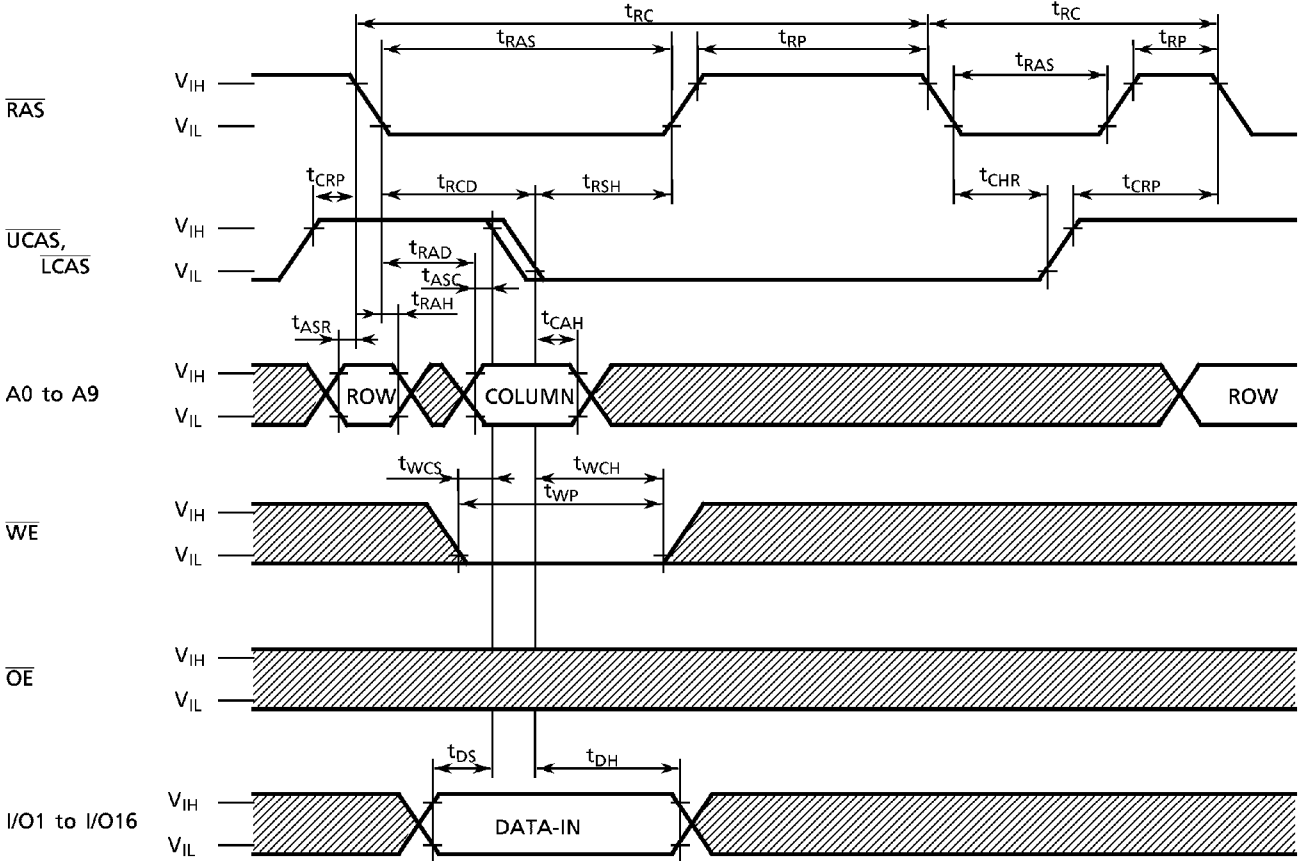
HIDDEN REFRESH CYCLE (READ)



Note: $D_{IN} = \text{Hi-Z}$

-  : H or L
-  : Invalid Data

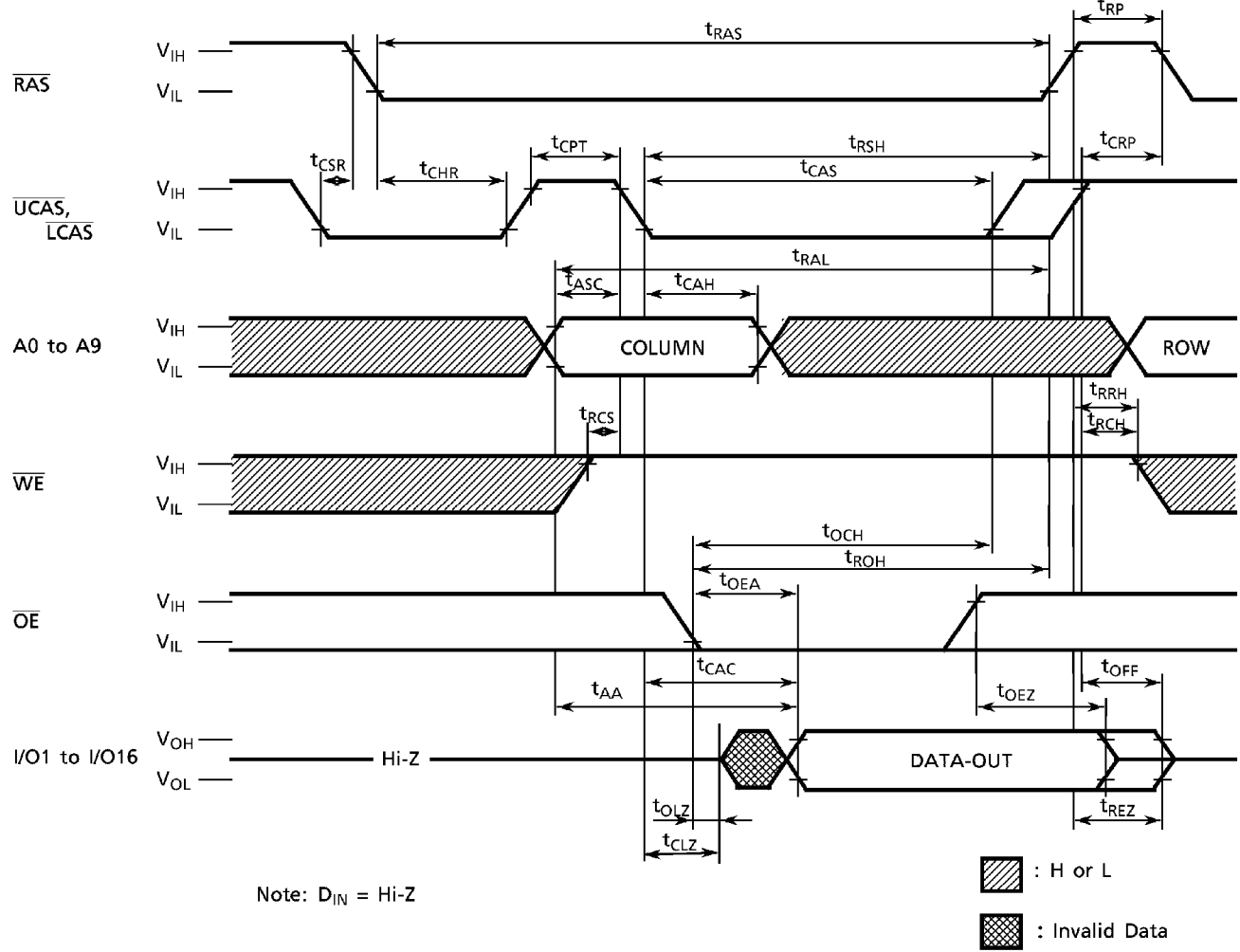
HIDDEN REEFRESH CYCLE (WRITE)



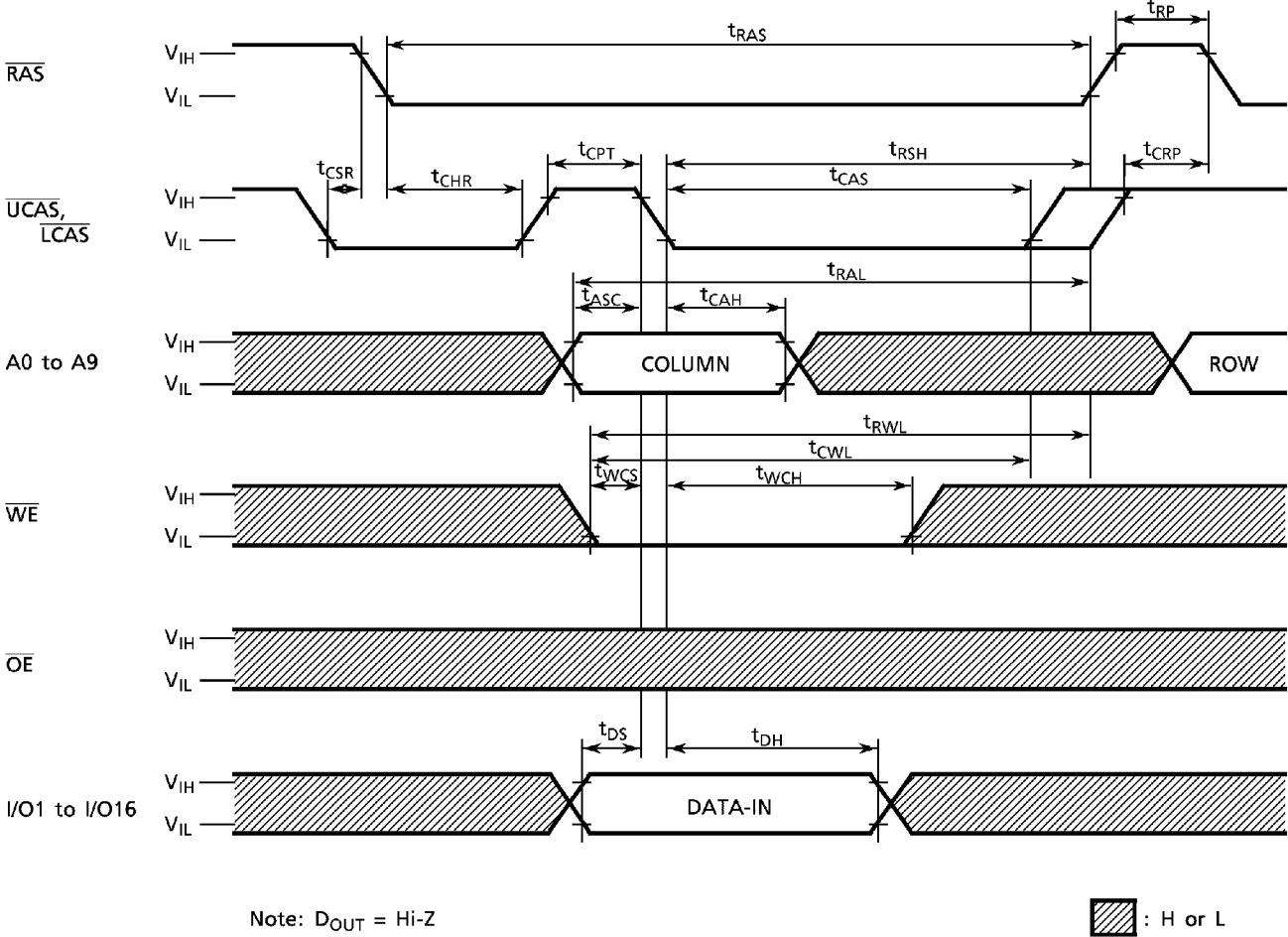
Note: $D_{OUT} = Hi-Z$

▨ : H or L

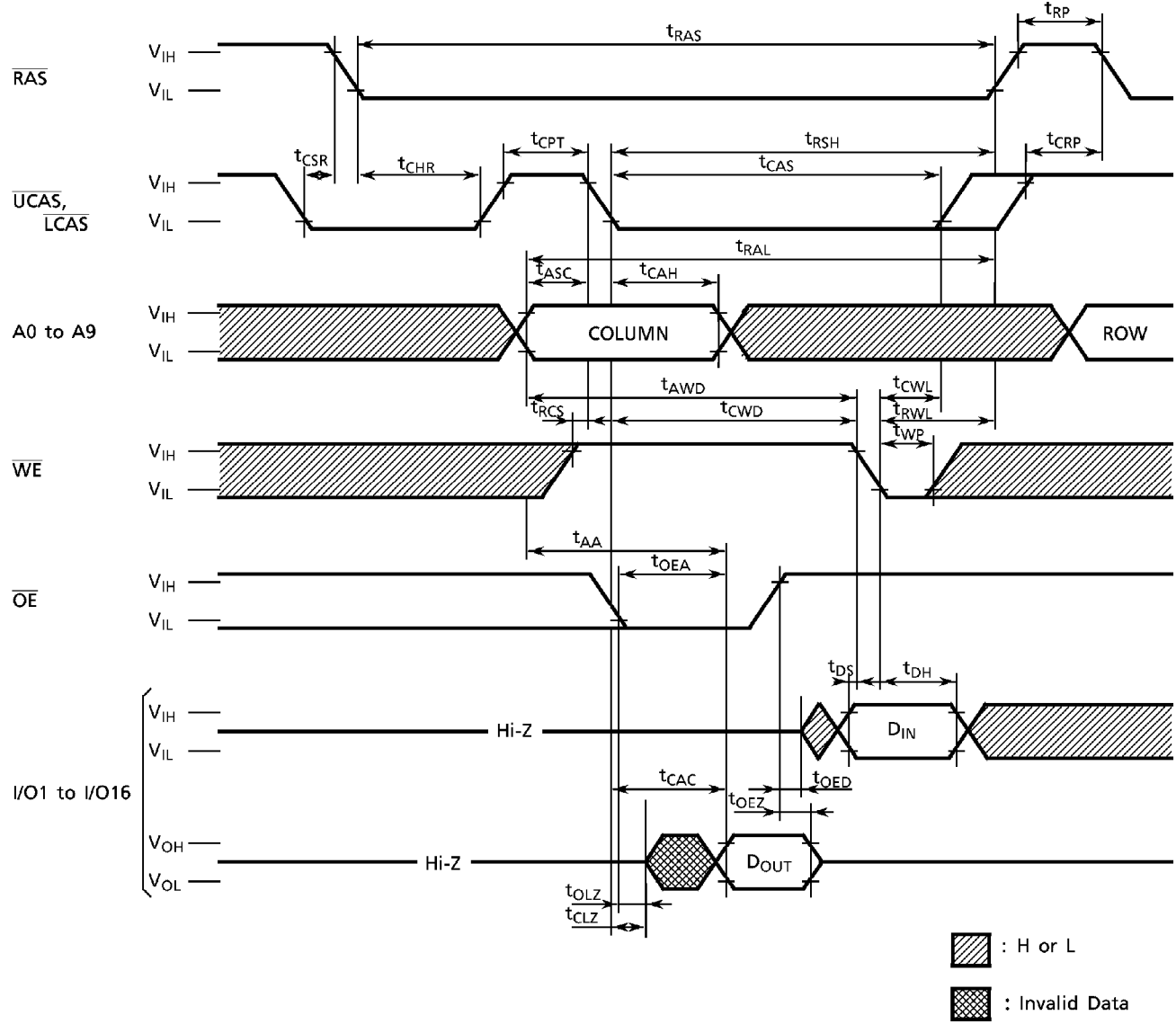
CAS-BEFORE-RAS REFRESH-COUNTER TEST READ CYCLE



CAS-BEFORE-RAS REFRESH-COUNTER TEST WRITE CYCLE

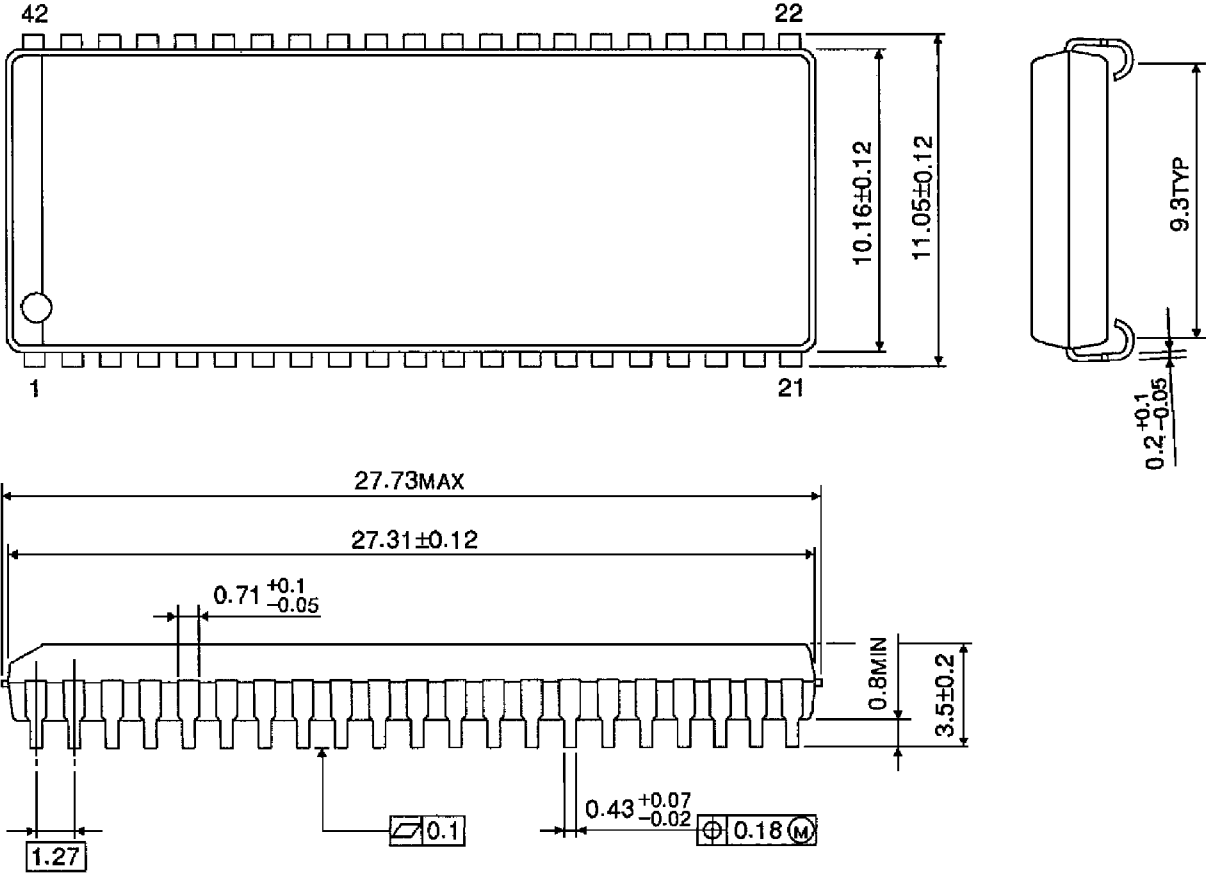


CAS-BEFORE-RAS REFRESH-COUNTER TEST READ-MODIFY-WRITE CYCLE



OUTLINE DRAWING (SOJ42-P-400-1.27)

Unit: mm



OUTLINE DRAWING (TSOPII 50/44-P-400-0.80)

Unit: mm

